TOSHIBA Photocoupler GaAlAs Ired & Photo-Diode Array

TLP590B

Telecommunication
Programmable Controllers
Mos Gate Driver
MOS FET Gate Driver

The TOSHIBA TLP590B consists of an aluminum galium arsenide infrared emitting diode optically coupled to a series connected photodiode array in a six lead plastic DIP package. TLP590B is suitable for MOS FET gate driver.

• UL recognized: UL1577, file No. E67349

Short Current

Туре	Classification	Short Current		Marking Of
Name	Classification	(min.)	l _F	Classification
TLP590B	C20	20μΑ	10mA	20
12. 3005	Standard 12µA		10/11/7	20, blank

(Note) Application type name for certification test, please use standard product type name, i.e.

TLP590B(C20): TLP590B

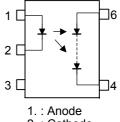
Weight: 0.39g

Maximum Ratings (Ta = 25°C)

	Characteristics	Symbol	Rating	Unit
	Forward current	ΙF	50	mA
	Forward current derating (Ta ≥ 25°C)	ΔI _F / °C	-0.5	mA / °C
LED	Pulse forward current (100µs pulse, 100 pps)	I _{FP}	1	Α
	Reverse voltage	V _R	3	٧
	Junction temperature	Tj	125	°C
or	Foward current	I _{FD}	50	μA
Detector	Reverse voltage	V_{RD}	10	V
ă	Junction temperature	Тj	125	°C
Sto	rage temperature range	T _{stg}	-55~125	°C
Оре	erating temperature range	T _{opr}	-40~85	°C
	d soldering temperature sec.)	T _{sol}	260	°C
	ation voltage ;, 1 min., R.H. ≤ 60%) (Note 1)	BV _S	2500	Vrms

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together, and pins 4 and 6 shorted together.

Pin Configuration(top view)



2. : Cathode 3. : NC 4. : Cathode 6. : Anode

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Forward current	IF	_	20	25	mA
Operating temperature	T _{opr}	-25	_	85	°C

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 10 mA	1.2	1.4	1.7	V
LED	Reverse current	I _R	V _R = 3 V	_	_	10	μΑ
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	60	pF
_	Forward voltage	V _{FD}	I _{FD} = 10 μA	_	7	_	V
Detector	Reverse current	I _{RD}	V _{RD} = 10 V	_	1	_	nA
Det	Capacitance (anode to cathode)	C _{TD}	V = 0, f = 1 MHz		_	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Open voltage	V _{OC}	I _F = 10 mA	7.0	8.0	_	V
Short current	I _{SC}	I _F = 10 mA	12	20	_	μΑ

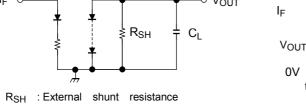
Isolation Characteristics (Ta = 25°C)

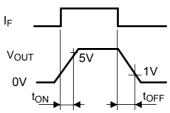
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	Cs	V _S = 0, f = 1 MHz	_	8.0	_	pF
Isolation resistance	R _S	V _S = 500 V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	_	Ω
Isolation voltage		AC, 1 minute 2500 —	_	Vrms		
	BV_S	AC, 1 second in oil	_	5000	_	VIIIIS
		DC, 1 minute in oil	_	5000	_	Vdc

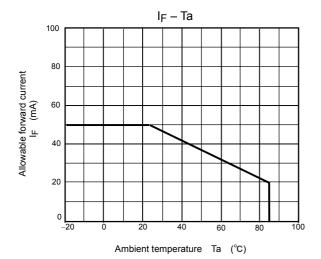
Switching Characteristics (Ta = 25°C)

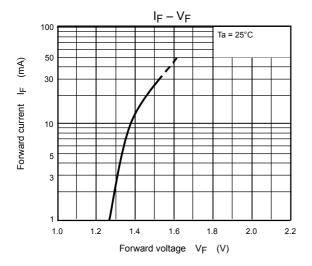
Characteristic	Symbol	Test Condition		Min.	Тур.	Max.	Unit
Turn-on time	t _{on}	I_F = 20mA, R_{SH} = 510kΩ		_	0.2	-	ms
Turn-off time	t _{off}	C _L =1000pF	(Fig.1)	_	1		ms

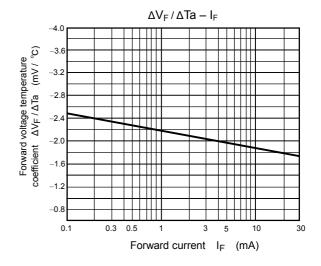
Fig. 1 Switching time test circuit

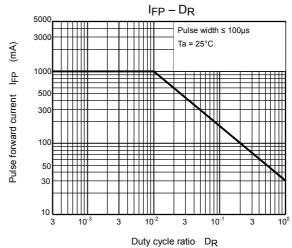


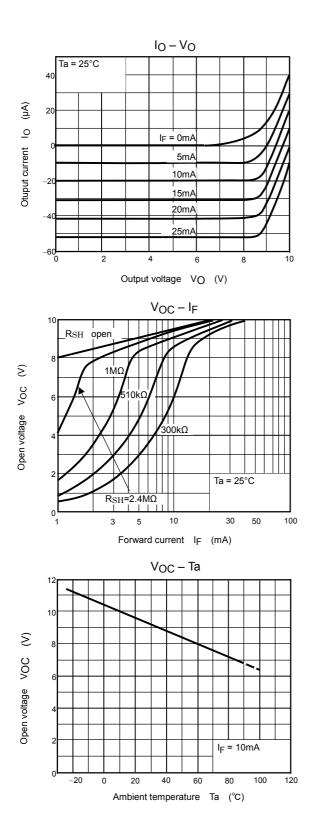


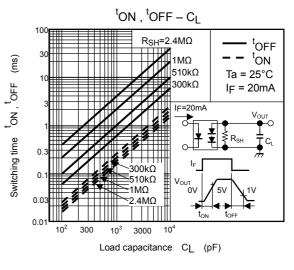


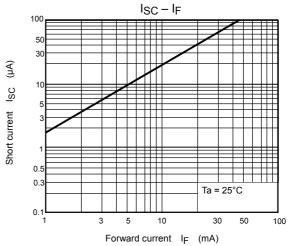


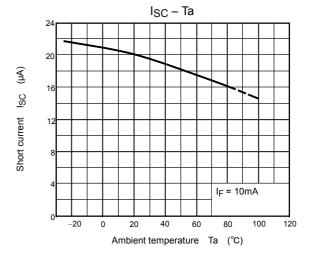












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